

Power Transistor (50V, 3A)

2SD1760 / 2SD1864

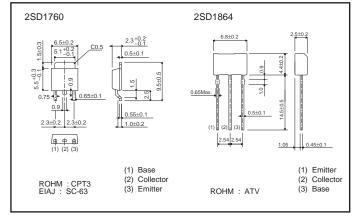
Features

- 1) Low V_{CE(sat)}. V_{CE(sat)} = 0.5V (Typ.) (I_C/I_B = 2A / 0.2A)
- 2) Complements the 2SB1184 / 2SB1243.

Structure

Epitaxial planar type NPN silicon transistor

•Dimensions (Unit : mm)



•Absolute maximum ratings (Ta=25°C)

		• • •			
Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	60	V	
Collector-emitter voltage		Vceo	50	V	
Emitter-base voltage		Vebo	5	V	
			3	A (DC)	
Collector current		lc	4.5	A (Pulse) *1	
Collector power	2SD1760	P	15	W (Tc=25°C)*2	
dissipation	2SD1864	Pc	1	W	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

*1 Single pulse, Pw=100ms

*2 Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	60	-	-	V	Ic=50μA	
Collector-emitter breakdown voltage	BVCEO	50	-	-	V	Ic=1mA	
Emitter-base breakdown voltage	ВVево	5	-	-	V	Iε=50μA	
Collector cutoff current	Ісво	_	-	1	μA	Vcb=40V	
Emitter cutoff current	Іево	-	-	1	μΑ	Veb=4V	
Collector-emitter saturation voltage	VCE (sat)	-	0.5	1	V	Ic/Iв=2А/0.2А	*
DC current transfer ratio	hfe	120	-	390	-	Vce=3V, Ic=0.5A	*
Transition frequency	fт	-	90	-	MHz	Vce=5V, Ie=-500mA, f=30MHz	*
Output capacitance	Cob	-	40	-	pF	Vсв=10V, Ie=0A, f=1MHz	

* Measured using pulse current.

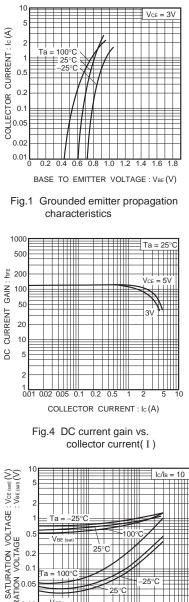
	9 - 1		· –	
		Package	Тар	oing
		Code	TL	TV2
Туре	hfe	Basic ordering unit (pieces)	2500	2500
2SD1760	QR		0	-
2SD1864	QR		-	0

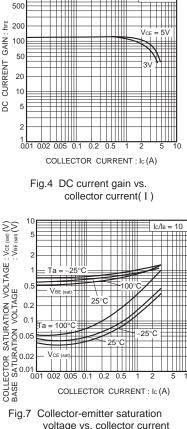
Packaging specifications and hre

hFE values are classified as follows:

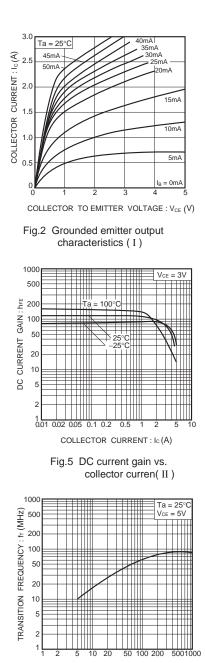
Item	Q	R	
hfe	120 to 270	180 to 390	

•Electrical characteristic curves



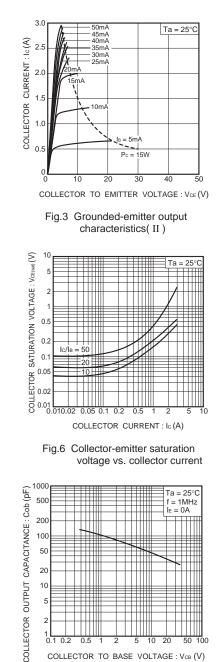


voltage vs. collector current Base-emitter saturation voltage vs. collector current



EMITTER CURRENT : -IE (mA)

Fig.8 Gain bandwidth product vs. emitter current



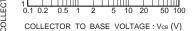
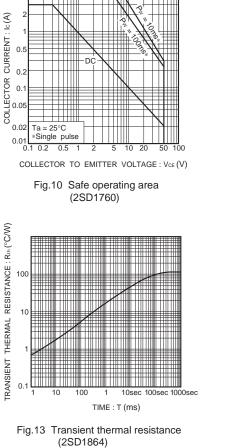


Fig.9 Collector output capacitance vs. collector-base voltage

2SD1760 / 2SD1864



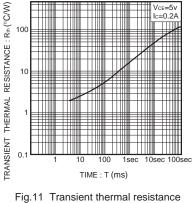


Fig.11 Transient thermal resistance (2SD1760)

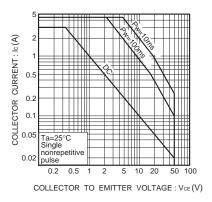


Fig.12 Safe operating area (2SD1864)

	Notes
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